Achim Trampert

List of Publications by Year
in descending order

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261	8,843	53794	56724
papers	citations	45 h-index	83 g-index

265	265	265	6527
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Crystal Phase Control during Epitaxial Hybridization of IIIâ€V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	5.1	18
2	SnO/Î²-Ga2O3 heterojunction field-effect transistors and vertical pâ€“n diodes. Applied Physics Letters, 2022, 120, .	3.3	12
3	Interface Recombination in Ga- and N-Polar GaN/(Al,Ga)N Quantum Wells Grown by Molecular Beam Epitaxy. Physical Review Applied, 2022, 17, .	3.8	2
4	Application of electron tomography for comprehensive determination of III-V interface properties. Ultramicroscopy, 2021, 224, 113261.	1.9	4
5	In Situ Transmission Electron Microscopy of Disorderâ€“Order Transition in Epitaxially Stabilized FeGe₂. Journal of Physical Chemistry C, 2021, 125, 2779-2784.	3.1	0
6	Drastic Effect of Sequential Deposition Resulting from Flux Directionality on the Luminescence Efficiency of Nanowire Shells. ACS Applied Materials & Interfaces, 2021, 13, 50220-50227.	8.0	1
7	Coaxial GaAs/(In,Ga)As Dot-in-a-Well Nanowire Heterostructures for Electrically Driven Infrared Light Generation on Si in the Telecommunication O Band. ACS Applied Nano Materials, 2020, 3, 165-174.	5.0	14
8	Strategies for Analyzing Noncommonâ€Atom Heterovalent Interfaces: The Case of CdTeâ€onâ€InSb. Advanced Materials Interfaces, 2020, 7, 1901658.	3.7	11
9	Nucleation Chronology and Electronic Properties of InAs_{1â€“xâ€“y}Sb_xP_y Graded Composition Quantum Dots Grown on an InAs(100) Substrate. ACS Applied Electronic Materials, 2020, 2, 646-650.	4.3	2
10	Interfacial resistance switching characteristics in metal-chalcogenide junctions using Biâ€“Cuâ€“Se, Biâ€“Agâ€“Se, and Sbâ€“Cuâ€“Te alloys. Journal of Alloys and Compounds, 2020, 824, 153880.	5.5	7
11	Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. Journal of Crystal Growth, 2019, 525, 125189.	1.5	7
12	Electron Tomography of Pencil-Shaped GaN/(In,Ga)N Core-Shell Nanowires. Nanoscale Research Letters, 2019, 14, 232.	5.7	5
13	Memristive resistive switch based on spontaneous barrier creation in metal-chalcogenide junctions. Journal Physics D: Applied Physics, 2019, 52, 385101.	2.8	8
14	GaSbBi Alloys and Heterostructures: Fabrication and Properties. Springer Series in Materials Science, 2019, , 125-161.	0.6	1
15	Molecular-beam epitaxy of GaInSbBi alloys. Journal of Applied Physics, 2019, 126, .	2.5	6
16	Lattice matched Volmerâ€“Weber growth of Fe₃Si on GaAs(001)â€”the influence of the growth rate. Semiconductor Science and Technology, 2019, 34, 124002.	2.0	1
17	Bismuth-surfactant-induced growth and structure of InAs/GaAs(110) quantum dots. Semiconductor Science and Technology, 2019, 34, 105016.	2.0	6
18	Impact of Bi incorporation on the evolution of microstructure during growth of low-temperature GaAs:Bi/Ga(As,Bi) layers. Journal of Applied Physics, 2019, 126, 085305.	2.5	7

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19	Toward heterostructured transition metal hybrids with highly promoted electrochemical hydrogen evolution. RSC Advances, 2019, 9, 19924-19929.	3.6	4
20	Interfacial reactions during the molecular beam epitaxy of GaN nanowires on Ti/Al₂O₃. Nanotechnology, 2019, 30, 114001.	2.6	13
21	In situ transmission electron microscopy of solid phase epitaxy of Ge on Fe₃Si. Semiconductor Science and Technology, 2019, 34, 124004.	2.0	3
22	Li2SnO3 branched nano- and microstructures with intense and broadband white-light emission. Nano Research, 2019, 12, 441-448.	10.4	7
23	Excitonic Aharonovâ€“Bohm Oscillations in Coreâ€“Shell Nanowires. Advanced Materials, 2019, 31, 1805645.	21.0	14
24	3D GaN Fins as a Versatile Platform for aâ€Planeâ€Based Devices. Physica Status Solidi (B): Basic Research, 2019, 256, 1800477.	1.5	7
25	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. Applied Physics Letters, 2018, 112, .	3.3	14
26	Manifestation of axiotaxy induced by the (10.4) plane in high-temperature-grown bismuth telluride films on InP(111). CrystEngComm, 2018, 20, 983-989.	2.6	1
27	Phase Stability and Anisotropic Sublimation of Cubic Geâ€“Sbâ€“Te Alloy Observed by In Situ Transmission Electron Microscopy. Journal of Physical Chemistry C, 2018, 122, 2968-2974.	3.1	9
28	Crystal-Phase Quantum Wires: One-Dimensional Heterostructures with Atomically Flat Interfaces. Nano Letters, 2018, 18, 247-254.	9.1	7
29	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. Acta Materialia, 2018, 143, 121-129.	7.9	12
30	Thermal expansion of single-crystalline Î²-Ga2O3 from RT to 1200â€‰K studied by synchrotron-based high resolution x-ray diffraction. Applied Physics Letters, 2018, 113, .	3.3	15
31	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. Semiconductor Science and Technology, 2018, 33, 094006.	2.0	4
32	Growth mode evolution during (100)-oriented Î²-Ga₂O₃ homoepitaxy. Nanotechnology, 2018, 29, 395705.	2.6	12
33	Ordered structure of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>FeGe</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math> formed during solid-phase epitaxy. Physical Review Materials, 2018, 2, .	2.4	4
34	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. Scripta Materialia, 2017, 132, 5-8.	5.2	9
35	Growth of GaP and AlGaP on GaP(1 1 1)B using gas-source molecular-beam-epitaxy. Journal of Crystal Growth, 2017, 477, 91-96.	1.5	1
36	Tailoring of microstructure and optoelectronic properties of Aluminum doped Zinc Oxide changing gun tilt. Materials Science in Semiconductor Processing, 2017, 63, 115-121.	4.0	8

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37	e and Composition of Isolated Core-Shell<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq1 1 0.784314 rg 31 mathvariant="normal">N</mml:mi><mml:mo>/</mml:mo><mml:mi>GaN</mml:mi></mml:mrow></mml:math>Rods Based on Nanofocus X-Ray Diffraction and Scanning Transmission Electron Microscopy. Physical Review	3.8	12
38	Morphological and chemical instabilities of nitrogen delta-doped GaAs/(Al, Ga)As quantum wells. Applied Physics Letters, 2017, 110, 201906.	3.3	3
39	GaSbBi/GaSb quantum well laser diodes. Applied Physics Letters, 2017, 110, .	3.3	45
40	Toward edges-rich MoS₂ layers via chemical liquid exfoliation triggering distinctive magnetism. Materials Research Letters, 2017, 5, 267-275.	8.7	19
41	Growth of Fe3Si/Ge/Fe3Si trilayers on GaAs(001) using solid-phase epitaxy. Applied Physics Letters, 2017, 110, .	3.3	22
42	Supernormal hardness increase of dilute Ga(As, N) thin films. Journal of Applied Physics, 2017, 121, 095105.	2.5	1
43	Polarity-Induced Selective Area Epitaxy of GaN Nanowires. Nano Letters, 2017, 17, 63-70.	9.1	18
44	Anomalous Strain Relaxation in Coreâ€“Shell Nanowire Heterostructures via Simultaneous Coherent and Incoherent Growth. Nano Letters, 2017, 17, 136-142.	9.1	35
45	Phase formation and strain relaxation of Ga2O3 on c-plane and a-plane sapphire substrates as studied by synchrotron-based x-ray diffraction. Applied Physics Letters, 2017, 111, .	3.3	58
46	Study of 3D-growth conditions for selective area MOVPE of high aspect ratio GaN fins with non-polar vertical sidewalls. Journal of Crystal Growth, 2017, 476, 90-98.	1.5	17
47	Continuous tuning of two-section, single-mode terahertz quantum-cascade lasers by fiber-coupled, near-infrared illumination. AIP Advances, 2017, 7, .	1.3	6
48	Strain Driven Shape Evolution of Stacked (In,Ga)N Quantum Disks Embedded in GaN Nanowires. Nano Letters, 2017, 17, 4654-4660.	9.1	6
49	Molecular Beam Epitaxy of GaN Nanowires on Epitaxial Graphene. Nano Letters, 2017, 17, 5213-5221.	9.1	72
50	Metalâ€“Semiconductor Phaseâ€Transition in WSe<sub>2(1â€_x₎Te₂_x Monolayer. Advanced Materials, 2017, 29, 1603991.	21.0	123
51	Liquid-solid phase transition of Ge-Sb-Te alloy observed by in-situ transmission electron microscopy. Ultramicroscopy, 2017, 178, 27-32.	1.9	4
52	The Role of Epitaxial Strain on the Spontaneous Formation of Bi-Rich Nanostructures in Ga(As,Bi) Epilayers and Quantum Wells. Nanoscience and Nanotechnology Letters, 2017, 9, 1132-1138.	0.4	5
53	Structural properties of Co2TiSi films on GaAs(001). Journal of Applied Physics, 2016, 120, .	2.5	1
54	Counterintuitive strain distribution in axial (In,Ga)N/GaN nanowires. Applied Physics Letters, 2016, 108, .	3.3	14

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55	Bowing effect in elastic constants of dilute Ga(As,N) alloys. Applied Physics Letters, 2016, 108, .	3.3	2
56	Molecular beam epitaxy of single crystalline GaN nanowires on a flexible Ti foil. Applied Physics Letters, 2016, 108, .	3.3	79
57	Strain dynamics during La2O3/Lu2O3 superlattice and alloy formation. Journal of Applied Physics, 2016, 119, 215301.	2.5	1
58	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. Applied Physics Reviews, 2016, 3, .	11.3	105
59	Diffraction at GaAs/Fe3Si core/shell nanowires: The formation of nanofacets. AIP Advances, 2016, 6, .	1.3	2
60	Exciton recombination at crystal-phase quantum rings in GaAs/InxGa1â^'xAs core/multishell nanowires. Applied Physics Letters, 2016, 109, .	3.3	10
61	Growth and stability of rocksalt Zn1â^'xMgxO epilayers and ZnO/MgO superlattice on MgO (100) substrate by molecular beam epitaxy. Journal of Chemical Physics, 2016, 144, 214704.	3.0	13
62	Spontaneous formation of three-dimensionally ordered Bi-rich nanostructures within GaAs_{1â^'x}Bi_x/GaAs quantum wells. Nanotechnology, 2016, 27, 325603.	2.6	27
63	Nature of excitons bound to inversion domain boundaries: Origin of the 3.45-eV luminescence lines in spontaneously formed GaN nanowires on Si(111). Physical Review B, 2016, 94, .	3.2	10
64	Nanofocus x-ray diffraction and cathodoluminescence investigations into individual coreâ€“shell (In,Ga)N/GaN rod light-emitting diodes. Nanotechnology, 2016, 27, 325707.	2.6	18
65	Observation of Dielectrically Confined Excitons in Ultrathin GaN Nanowires up to Room Temperature. Nano Letters, 2016, 16, 973-980.	9.1	40
66	Perpendicular magnetic anisotropy in the Heusler alloy Co2TiSi/GaAs(001) hybrid structure. AIP Advances, 2015, 5, 057130.	1.3	5
67	Electron tomography of (In,Ga)N insertions in GaN nanocolumns grown on semi-polar (112Ì„2) GaN templates. APL Materials, 2015, 3, 036102.	5.1	3
68	Detecting lateral composition modulation in dilute Ga(As,Bi) epilayers. Nanotechnology, 2015, 26, 425701.	2.6	16
69	Correlation among Growth Conditions, Morphology, and Optical Properties of Nanocolumnar InGaN/GaN Heterostructures Selectively Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2015, 15, 2661-2666.	3.0	17
70	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. Optics Express, 2015, 23, 29423.	3.4	10
71	Facetted growth of Fe3Si shells around GaAs nanowires on Si(111). Journal of Crystal Growth, 2015, 427, 21-23.	1.5	8
72	Spontaneous formation of nanostructures by surface spinodal decomposition in GaAs1â^'xBix epilayers. Journal of Applied Physics, 2015, 117, .	2.5	25

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73	Interface structure and strain state of InAs nano-clusters embedded in silicon. Acta Materialia, 2015, 90, 133-139.	7.9	16
74	Electron tomography on nanopores embedded in epitaxial GaSb thin films. Micron, 2015, 73, 54-62.	2.2	11
75	Molecular beam epitaxy growth and properties of Co2TiSi thin films on GaAs(0â€‰0â€‰1): the effect of growth temperature. Journal Physics D: Applied Physics, 2015, 48, 025003.	2.8	6
76	Real structure of lattice matched GaAsâ€“Fe3Si coreâ€“shell nanowires. Journal of Crystal Growth, 2015, 410, 1-6.	1.5	6
77	Formation and phase transformation of Bi-containing QD-like clusters in annealed GaAsBi. Nanotechnology, 2014, 25, 205605.	2.6	44
78	Observation of atomic ordering of triple-period-A and -B type in GaAsBi. Applied Physics Letters, 2014, 105, 041602.	3.3	33
79	Axial InAs/GaAs heterostructures on silicon in a nanowire geometry. Nanotechnology, 2014, 25, 485602.	2.6	1
80	Lattice-engineered Si1-xGex-buffer on Si(001) for GaP integration. Journal of Applied Physics, 2014, 115, 103501.	2.5	10
81	Plan-view transmission electron microscopy investigation of GaAs/(In,Ga)As core-shell nanowires. Applied Physics Letters, 2014, 105, 121602.	3.3	16
82	Epitaxial polymorphism of La2O3 on Si(111) studied by in situ x-ray diffraction. Applied Physics Letters, 2014, 105, .	3.3	10
83	Epitaxial Fe3Si/Ge/Fe3Si thin film multilayers grown on GaAs(001). Thin Solid Films, 2014, 556, 120-124.	1.8	20
84	Magnetic properties of Gdâ€doped GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 1673-1684.	1.5	13
85	Coaxial Multishell (In,Ga)As/GaAs Nanowires for Near-Infrared Emission on Si Substrates. Nano Letters, 2014, 14, 2604-2609.	9.1	111
86	Atomistic structure and energetics of GdN clusters in Gd-doped GaN. Acta Materialia, 2014, 76, 87-93.	7.9	4
87	Investigation of IIIâ€“V Nanowires by Plan-View Transmission Electron Microscopy: InN Case Study. Microscopy and Microanalysis, 2014, 20, 1471-1478.	0.4	5
88	Control over the Number Density and Diameter of GaAs Nanowires on Si(111) Mediated by Droplet Epitaxy. Nano Letters, 2013, 13, 3607-3613.	9.1	41
89	Nanoscale Imaging of InN Segregation and Polymorphism in Single Vertically Aligned InGaN/GaN Multi Quantum Well Nanorods by Tip-Enhanced Raman Scattering. Nano Letters, 2013, 13, 3205-3212.	9.1	37
90	In situ doping of catalyst-free InAs nanowires with Si: Growth, polytypism, and local vibrational modes of Si. Applied Physics Letters, 2013, 103, .	3.3	15

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91	GaAsâ€“Fe₃Si Coreâ€“Shell Nanowires: Nanobar Magnets. Nano Letters, 2013, 13, 6203-6209.	9.1	13
92	Mono- and few-layer nanocrystalline graphene grown on Al2O3(0 0 0 1) by molecular beam epitaxy. Carbon, 2013, 56, 339-350.	10.3	54
93	Coherent GdN clusters in epitaxial GaN:Gd thin films determined by transmission electron microscopy. Nanotechnology, 2013, 24, 255701.	2.6	7
94	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. Applied Physics Letters, 2013, 102, .	3.3	16
95	Oxygen-Deficient Oxide Growth by Subliming the Oxide Source Material: The Cause of Silicide Formation in Rare Earth Oxides on Silicon. Crystal Growth and Design, 2013, 13, 3645-3650.	3.0	11
96	Monolithic integration of InGaN segments emitting in the blue, green, and red spectral range in single ordered nanocolumns. Applied Physics Letters, 2013, 102, 181103.	3.3	39
97	Selective area growth and characterization of GaN nanocolumns, with and without an InGaN insertion, on semi-polar (11â€“22) GaN templates. Applied Physics Letters, 2013, 103, .	3.3	15
98	Selective area growth of In(Ga)N/GaN nanocolumns by molecular beam epitaxy on GaN-buffered Si(111): from ultraviolet to infrared emission. Nanotechnology, 2013, 24, 175303.	2.6	54
99	Atomic interface structure of bixbyite rare-earth sesquioxides grown epitaxially on Si(1â€‰1â€‰1). Journal Physics D: Applied Physics, 2012, 45, 295302.	2.8	2
100	Formation of a Monocrystalline, M-Plane AlN Layer by the Nitridation of $gamma$-LiAlO$_{2}$(100). Applied Physics Express, 2012, 5, 105501.	2.4	5
101	Interface properties of (In,Ga)As/GaAs quantum wells grown by solid-phase epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B108.	1.2	4
102	Strain-induced composition limitation in nitrogen Î´-doped (In,Ga)As/GaAs quantum wells. Applied Physics Letters, 2012, 100, 171906.	3.3	4
103	ORDERED GAN/INGAN NANORODS ARRAYS GROWN BY MOLECULAR BEAM EPITAXY FOR PHOSPHOR-FREE WHITE LIGHT EMISSION. International Journal of High Speed Electronics and Systems, 2012, 21, 1250010.	0.7	7
104	Plasmon excitation in electron energy-loss spectroscopy for determination of indium concentration in (In,Ga)N/GaN nanowires. Nanotechnology, 2012, 23, 485701.	2.6	32
105	Selective area growth and characterization of InGaN nano-disks implemented in GaN nanocolumns with different top morphologies. Applied Physics Letters, 2012, 100, .	3.3	34
106	Spontaneous Nucleation and Growth of GaN Nanowires: The Fundamental Role of Crystal Polarity. Nano Letters, 2012, 12, 6119-6125.	9.1	106
107	Direct experimental determination of the spontaneous polarization of GaN. Physical Review B, 2012, 86, .	3.2	94
108	Scaling growth kinetics of self-induced GaN nanowires. Applied Physics Letters, 2012, 100, .	3.3	60

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109	Strain accommodation in Ga-assisted GaAs nanowires grown on silicon (111). Nanotechnology, 2012, 23, 305703.	2.6	33
110	Epitaxial phaseâ€change materials. Physica Status Solidi - Rapid Research Letters, 2012, 6, 415-417.	2.4	29
111	Residual disorder and diffusion in thin Heusler alloy films. Physical Review B, 2012, 86, .	3.2	6
112	Critical Role of Two-Dimensional Island-Mediated Growth on the Formation of Semiconductor Heterointerfaces. Physical Review Letters, 2012, 109, 126101.	7.8	35
113	Quantitative description for the growth rate of self-induced GaN nanowires. Physical Review B, 2012, 85, .	3.2	80
114	Scaling thermodynamic model for the self-induced nucleation of GaN nanowires. Physical Review B, 2012, 85, .	3.2	53
115	Delayed crystallization of ultrathin Gd2O3 layers on Si(111) observed by in situ X-ray diffraction. Nanoscale Research Letters, 2012, 7, 203.	5.7	14
116	Current path in light emitting diodes based on nanowire ensembles. Nanotechnology, 2012, 23, 465301.	2.6	50
117	E-beam nano-patterning for the ordered growth of GaN/InGaN nanorods. Microelectronic Engineering, 2012, 98, 374-377.	2.4	4
118	Insight into the Growth and Control of Single-Crystal Layers of Geâ€“Sbâ€“Te Phase-Change Material. Crystal Growth and Design, 2011, 11, 4606-4610.	3.0	34
119	Atomic Configuration of the MnAs/GaAs (110) Interface Analyzed by High-Resolution Electron Microscopy. Journal of Physical Chemistry C, 2011, 115, 529-533.	3.1	2
120	Formation of High-Quality GaN Microcrystals by Pendeoepitaxial Overgrowth of GaN Nanowires on Si(111) by Molecular Beam Epitaxy. Crystal Growth and Design, 2011, 11, 4257-4260.	3.0	30
121	Macro- and micro-strain in GaN nanowires on Si(111). Nanotechnology, 2011, 22, 295714.	2.6	61
122	N-face GaN nanorods: Continuous-flux MOVPE growth and morphological properties. Journal of Crystal Growth, 2011, 315, 164-167.	1.5	44
123	Understanding the selective area growth of GaN nanocolumns by MBE using Ti nanomasks. Journal of Crystal Growth, 2011, 325, 89-92.	1.5	97
124	The nanorod approach: GaN NanoLEDs for solid state lighting. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2296-2301.	0.8	128
125	Effect of indium incorporation on optical and structural properties of m-plane InGaN/GaN MQW on LiAlO2 substrates. Journal of Crystal Growth, 2011, 315, 246-249.	1.5	13
126	Distribution of Mn in ferromagnetic (In,Mn)Sb films grown on (001) GaAs using MBE. Journal of Crystal Growth, 2011, 323, 340-343.	1.5	0

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127	Interface engineering for improved growth of GaSb on Si(111). Journal of Crystal Growth, 2011, 323, 401-404.	1.5	24
128	Rare-earth oxide superlattices on Si(1 1 1). Journal of Crystal Growth, 2011, 323, 95-98.	1.5	4
129	Monodisperse (In, Ga)N insertions in catalyst-free-grown GaN(0001) nanowires. Nanotechnology, 2011, 22, 365703.	2.6	15
130	Polarity determination by electron energy-loss spectroscopy: application to ultra-small III-nitride semiconductor nanocolumns. Nanotechnology, 2011, 22, 415701.	2.6	29
131	Direct observation of N-(group V) bonding defects in dilute nitride semiconductors using hard x-ray photoelectron spectroscopy. Applied Physics Letters, 2011, 98, 121915.	3.3	10
132	Emission control of InGaN nanocolumns grown by molecular-beam epitaxy on Si(111) substrates. Applied Physics Letters, 2011, 99, .	3.3	29
133	Morphology and stress evolution of InAs QD grown and annealed in-situ at high temperature. Journal of Crystal Growth, 2010, 312, 447-451.	1.5	10
134	1.3Î¼m emitting GaInNAs/GaAs quantum well resonant cavity LEDs. Solid-State Electronics, 2010, 54, 492-496.	1.4	6
135	Anisotropic properties of MOVPE-grown m-plane GaN layers on LiAlO2 substrates. Physica Status Solidi (B): Basic Research, 2010, 247, 1750-1752.	1.5	2
136	GaN and ZnO nanostructures. Physica Status Solidi (B): Basic Research, 2010, 247, 2315-2328.	1.5	4
137	Long-range order and thermal stability of thin Co2FeSi films on GaAs(1â€‰1â€‰1)B. Journal Physics D: Applied Physics, 2010, 43, 285404.	2.8	6
138	Epitaxial growth and structure of (La1â^'xLux)2O3 alloys on Si(111). Applied Physics Letters, 2010, 97, 031911.	3.3	14
139	Epitaxial Heusler alloy Co₂FeSi films on Si(1â€‰1â€‰1) substrates grown by molecular beam epitaxy. Journal Physics D: Applied Physics, 2010, 43, 305004.	2.8	12
140	Continuous-flux MOVPE growth of position-controlled N-face GaN nanorods and embedded InGaN quantum wells. Nanotechnology, 2010, 21, 305201.	2.6	142
141	In situanalysis of strain relaxation during catalyst-free nucleation and growth of GaN nanowires. Nanotechnology, 2010, 21, 245705.	2.6	46
142	Striated surface morphology and crystal orientation of m-plane GaN films grown on Î³-LiAlO2(100). Applied Physics Letters, 2010, 96, 231914.	3.3	16
143	Collector Phase Transitions during Vaporâ^'Solidâ^'Solid Nucleation of GaN Nanowires. Nano Letters, 2010, 10, 3426-3431.	9.1	46
144	InN nanocolumns grown by plasma-assisted molecular beam epitaxy on A-plane GaN templates. Applied Physics Letters, 2009, 94, 221908.	3.3	9

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145	Metal-organic vapour-phase epitaxy of gallium nitride nanostructures for optoelectronic applications. Microelectronics Journal, 2009, 40, 333-335.	2.0	4
146	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1739-1744.	1.5	23
147	The role of Sb and N ions on the morphology and localization of (Ga,In) (N,As) quantum wells. Journal of Crystal Growth, 2009, 311, 1728-1732.	1.5	3
148	Carrier spin polarization in ferromagnetâ€“semiconductor (Ga,Mn)As/GaAs structures. Journal of Magnetism and Magnetic Materials, 2009, 321, 720-722.	2.3	4
149	Effects of nanowire coalescence on their structural and optical properties on a local scale. Applied Physics Letters, 2009, 95, .	3.3	84
150	Ge_{1-x} Mn_x Clusters: Central Structural and Magnetic Building Blocks of Nanoscale Wire-Like Self-Assembly in a Magnetic Semiconductor. Nano Letters, 2009, 9, 3743-3748.	9.1	37
151	On the mechanisms of spontaneous growth of III-nitride nanocolumns by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 4035-4045.	1.5	165
152	Vertical composition fluctuations in (Ga,In)(N,As) quantum wells grown on vicinal (111)B GaAs. Journal of Physics and Chemistry of Solids, 2008, 69, 343-346.	4.0	3
153	Composition fluctuations and clustering in (Ga,In)(N,As)/GaAs(001) heterostructures studied by analytical transmission electron microscopy. Journal of Physics and Chemistry of Solids, 2008, 69, 335-342.	4.0	3
154	Enhanced Performances of Quantum Dot Lasers Operating at 1.3 mu m. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1188-1196.	2.9	26
155	Gallium nitride heterostructures on 3D structured silicon. Nanotechnology, 2008, 19, 405301.	2.6	10
156	Indium distribution at the interfaces of (Ga,In)(N,As)âˆ•GaAs quantum wells. Applied Physics Letters, 2008, 92, .	3.3	24
157	Linear increase of the modal gain in 1.3 Âµm InAs/GaAs quantum dot lasers containing up to seven-stacked QD layers. Nanotechnology, 2008, 19, 275401.	2.6	12
158	Impact of carrier localization on the photoluminescence characteristics of (Ga,In)(N,As) and (Ga,In)(N,As,Sb) quantum wells. Journal of Applied Physics, 2008, 104, .	2.5	15
159	Type II transition in InSb-based nanostructures for midinfrared applications. Journal of Applied Physics, 2008, 103, 114516.	2.5	9
160	InAs/GaSb short-period superlattice injection lasers operating in 2.5â€…[micro sign]mâ€“3.5â€…[micro sign]m mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	1.0	15
161	Role of ionized nitrogen species in the optical and structural properties of GaInNAs/GaAs quantum wells grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2007, 101, 103526.	2.5	8
162	Molecular-beam epitaxy of InSb/GaSb quantum dots. Journal of Applied Physics, 2007, 101, 124309.	2.5	31

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